

N-Channel Power MOSFET

150V, 1.4A, 480mΩ

FEATURES

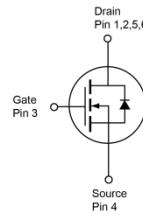
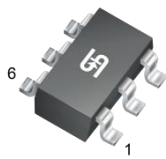
- Low $R_{DS(on)}$ to minimize conductive losses
- Low gate charge for fast power switching
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS

PARAMETER	VALUE	UNIT
V_{DS}	150	V
$R_{DS(on)}$ (max)	$V_{GS} = 10V$	480
	$V_{GS} = 6V$	520
Q_g	8	nC

APPLICATIONS

- Battery Management System
- LED Lighting


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Note: MSL 3 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Note 1)	$T_C = 25^\circ\text{C}$	1.4	A
	$T_A = 25^\circ\text{C}$	1.1	
Pulsed Drain Current	I_{DM}	5.6	A
Total Power Dissipation	$T_C = 25^\circ\text{C}$	2.1	W
	$T_C = 125^\circ\text{C}$	0.4	
Total Power Dissipation	$T_A = 25^\circ\text{C}$	1.5	W
	$T_A = 125^\circ\text{C}$	0.3	
Operating Junction and Storage Temperature Range	T_J, T_{STG}	- 55 to +150	$^\circ\text{C}$

THERMAL PERFORMANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	59	$^\circ\text{C/W}$
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	83	$^\circ\text{C/W}$

Thermal Performance Note: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	BV _{DSS}	150	--	--	V
Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 250μA	V _{GS(TH)}	2	2.9	3.5	V
Gate Threshold Voltage Temperature Coefficient	I _D = 250μA	$\frac{\Delta V_{GS(TH)}}{\Delta T_J}$	--	-6.4	--	mV/°C
Gate-Source Leakage Current	V _{GS} = ±20V, V _{DS} = 0V	I _{GSS}	--	--	±100	nA
Drain-Source Leakage Current	V _{GS} = 0V, V _{DS} = 150V	I _{DSS}	--	--	1	μA
	V _{GS} = 0V, V _{DS} = 150V T _J = 125°C		--	--	100	
Drain-Source On-State Resistance (Note 2)	V _{GS} = 10V, I _D = 1.1A	R _{DS(on)}	--	392	480	mΩ
	V _{GS} = 6V, I _D = 1.1A		--	428	520	
Forward Transconductance (Note 2)	V _{DS} = 5V, I _D = 1.1A	g _{fs}	--	3.3	--	S
Dynamic (Note 3)						
Total Gate Charge	V _{GS} = 10V, V _{DS} = 10V, I _D = 1.1A	Q _g	--	8	--	nC
Total Gate Charge	V _{GS} = 6V, V _{DS} = 10V, I _D = 1.1A	Q _g	--	5	--	
Gate-Source Charge		Q _{gs}	--	2	--	
Gate-Drain Charge		Q _{gd}	--	2.7	--	
Input Capacitance	V _{GS} = 0V, V _{DS} = 10V f = 1.0MHz	C _{iss}	--	332	--	pF
Output Capacitance		C _{oss}	--	20	--	
Reverse Transfer Capacitance		C _{rss}	--	1	--	
Gate Resistance	f = 1.0MHz	R _g	--	3.5	--	Ω
Switching (Note 3)						
Turn-On Delay Time	V _{GS} = 10V, V _{DS} = 10V, I _D = 1.1A, R _G = 2Ω,	t _{d(on)}	--	5	--	ns
Turn-On Rise Time		t _r	--	18	--	
Turn-Off Delay Time		t _{d(off)}	--	9	--	
Turn-Off Fall Time		t _f	--	18	--	
Source-Drain Diode						
Forward Voltage (Note 2)	V _{GS} = 0V, I _S = 1.1A	V _{SD}	--	--	1.2	V
Reverse Recovery Time	I _S = 1.1A , dI/dt = 100A/μs	t _{rr}	--	51	--	ns
Reverse Recovery Charge		Q _{rr}	--	59	--	nC

Notes:

1. Silicon limited current only.
2. Pulse test: Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Switching time is essentially independent of operating temperature.

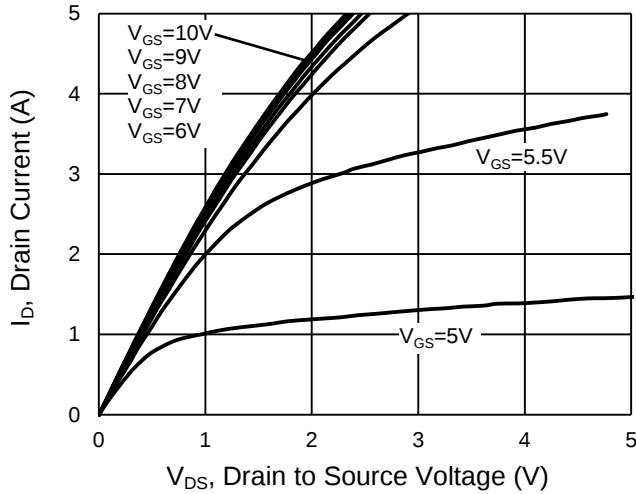
ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM4800N15CX6 RFG	SOT-26	3,000pcs / 7" Reel

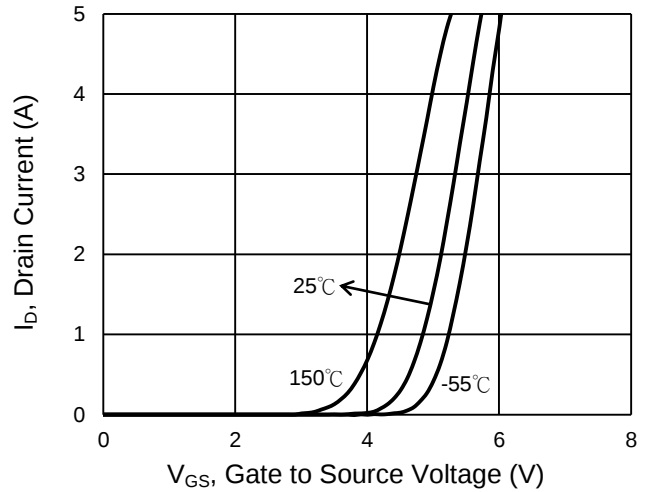
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

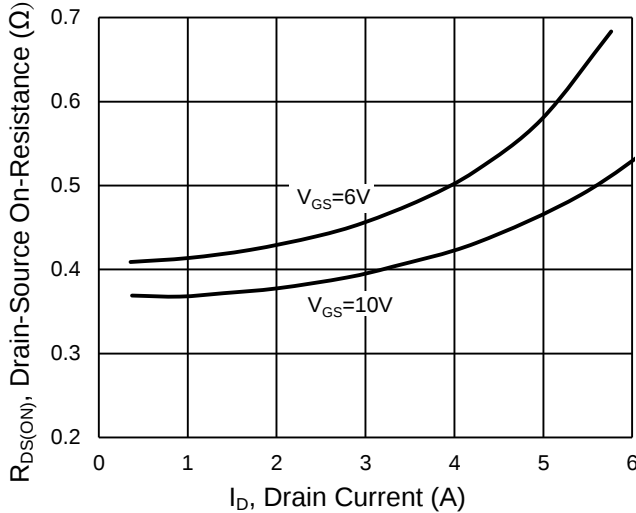
Output Characteristics



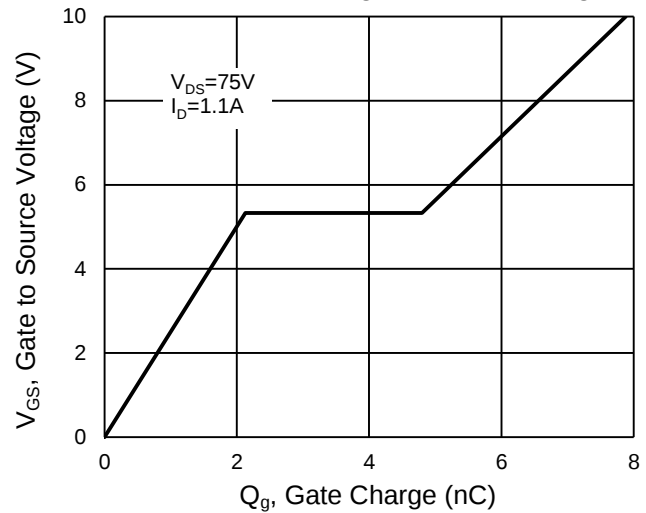
Transfer Characteristics



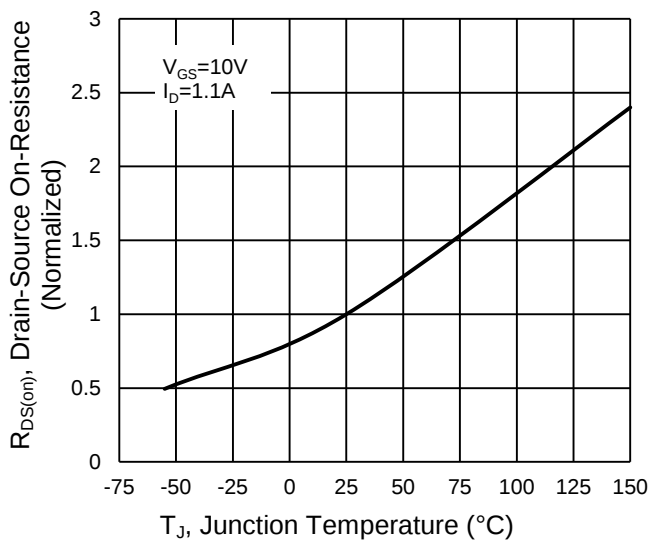
On-Resistance vs. Drain Current



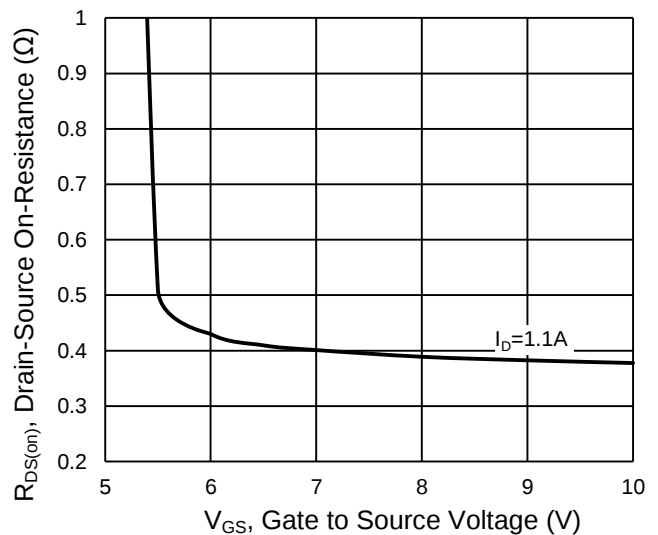
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



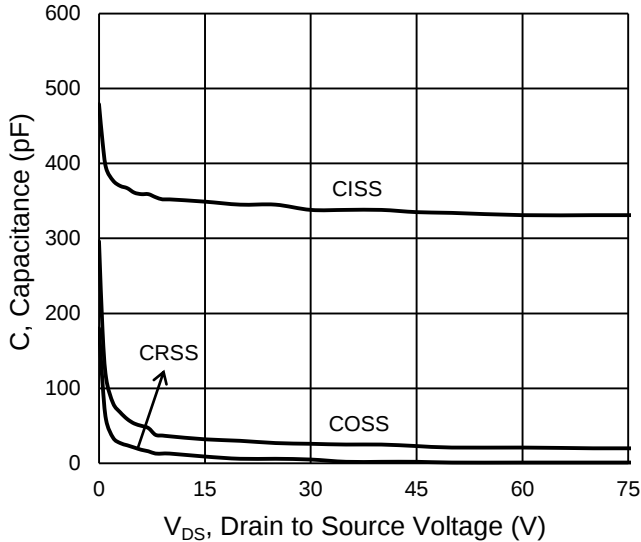
On-Resistance vs. Gate-Source Voltage



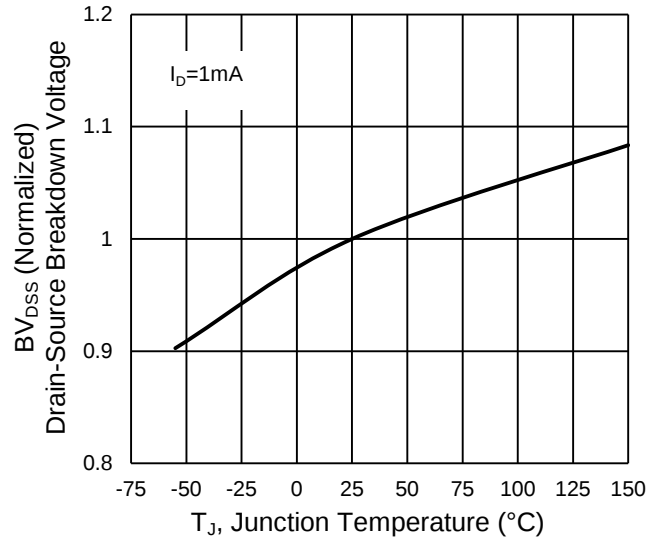
CHARACTERISTICS CURVES

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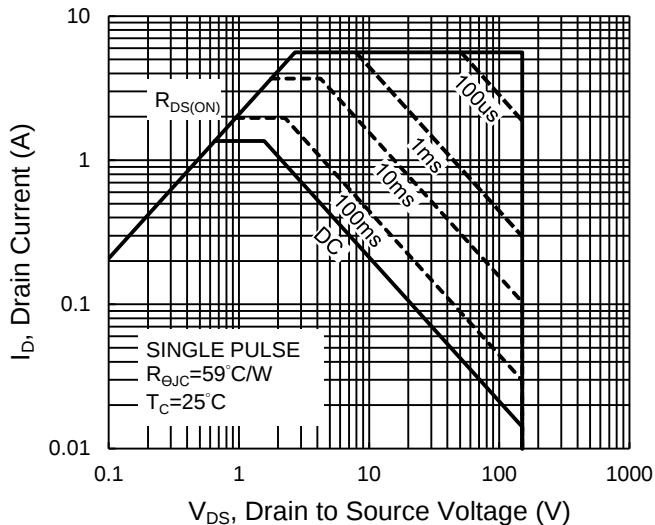
Capacitance vs. Drain-Source Voltage



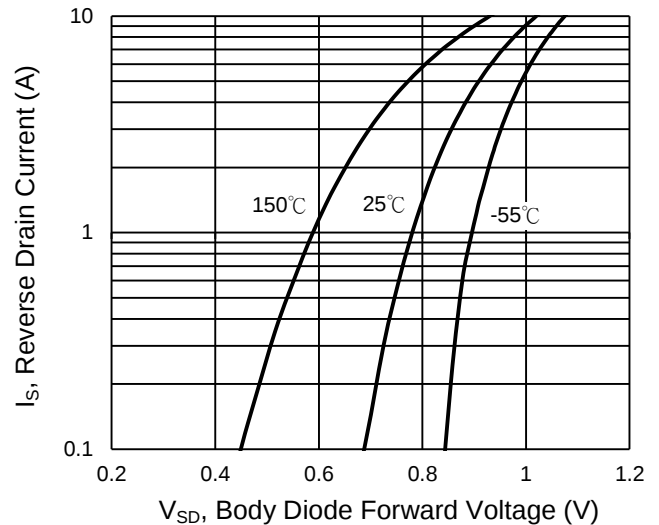
BV_{DSS} vs. Junction Temperature



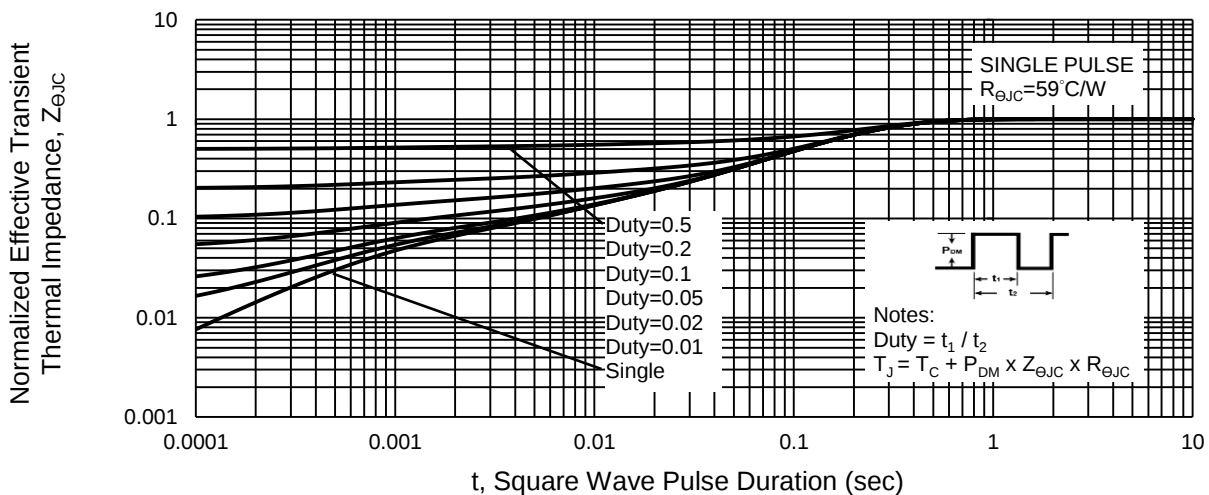
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage

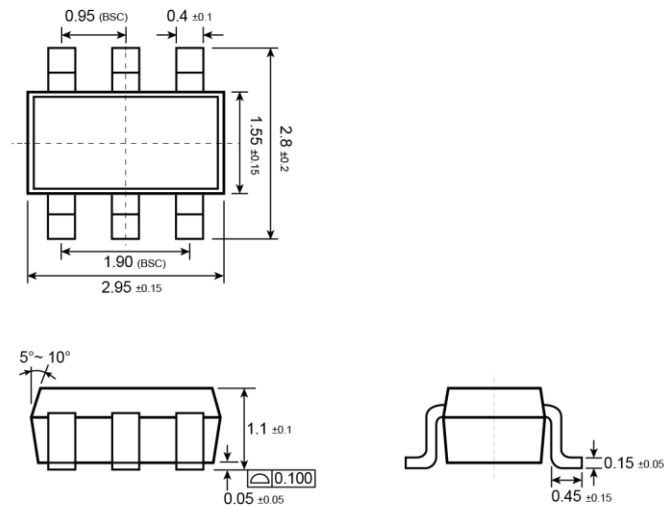


Normalized Thermal Transient Impedance, Junction-to-Case

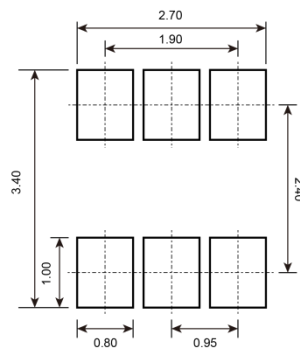


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

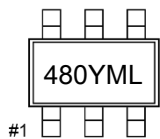
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SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



480 = Device Code

Y = Year Code

M = Month Code

O =Jan **P** =Feb **Q** =Mar **R** =Apr

S =May **T** =Jun **U** =Jul **V** =Aug

W =Sep **X** =Oct **Y** =Nov **Z** =Dec

L = Lot Code

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